



گروه فنی مهندسی جوش و برش مقدم

اعتماد از شما کیفیت و تخصص از ما



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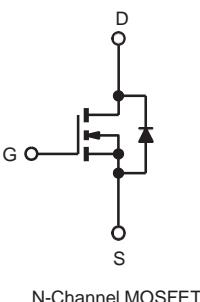
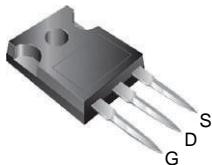


مشهد خیام شمالی 63 خیابان پردیس 3

برای کسب اطلاعات بیشتر بر روی لینک ها کلیک کنید

- 7 سال سابقه آموزش تعمیرات تخصصی دستگاه های جوش اینورتری تک فاز و 3 فاز
- 7 سال سابقه فروش قطعات الکترونیکی دستگاه جوش تک فاز و 3 فاز
- آموزش تخصصی تحلیل دستگاه های جوش اینورتری مختص ابراز فروشان
- آموزش تخصصی ابراز آلات شارژی

TO-247



PRODUCT SUMMARY

V_{DS} (V)	500	
$R_{DS(on)}$ (Λ)	$V_{GS} = 10$ V	0.27
Q_g (max.) (nC)	210	
Q_{gs} (nC)	29	
Q_{gd} (nC)	110	
Configuration	Single	

FEATURES

- Dynamic dV/dt rating
- Repetitive avalanche rated
- Isolated central mounting hole
- Fast switching
- Ease of paralleling
- Simple drive requirements
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details.

DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-247 package is preferred for commercial-industrial applications where higher power levels preclude the use of TO-220 devices. The TO-247 is similar but superior to the earlier TO-218 package because its isolated mounting hole. It also provides greater creepage distances between pins to meet the requirements of most safety specifications.

ORDERING INFORMATION

Package	TO-247
Lead (Pb)-free	IRFP460PbF

ABSOLUTE MAXIMUM RATINGS $T_C = 25$ °C, unless otherwise noted

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{DS}	500	V
Gate-source voltage	V_{GS}	± 20	
Continuous drain current	I_D	20	A
		13	
Pulsed drain current ^a	I_{DM}	80	W/°C
Linear derating factor		2.2	
Single pulse avalanche energy ^b	E_{AS}	960	mJ
Repetitive avalanche current ^a	I_{AR}	20	A
Repetitive avalanche energy ^a	E_{AR}	28	mJ
Maximum power dissipation	P_D	280	W
Peak diode recovery dV/dt ^c	dV/dt	3.5	V/ns
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +150	°C
Soldering recommendations (peak temperature)	for 10 s	300 ^d	
Mounting Torque	6-32 or M3 screw	10	lbf · in
		1.1	N · m

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- $V_{DD} = 50$ V, starting $T_J = 25$ °C, $L = 4.3$ mH, $R_G = 25 \Lambda$, $I_{AS} = 20$ A (see fig. 12)
- $I_{SD} \leq 20$ A, $dI/dt \leq 160$ A/ μ s, $V_{DD} \leq V_{DS}$, $T_J \leq 150$ °C
- 1.6 mm from case

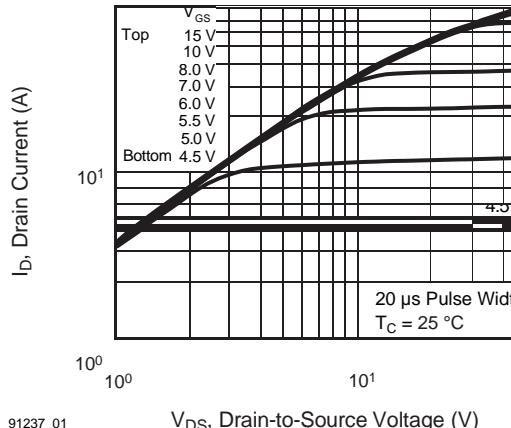
THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R_{thJA}	-	40	
Case-to-sink, flat, greased surface	R_{thCS}	0.24	-	
Maximum junction-to-case (drain)	R_{thJC}	-	0.45	

SPECIFICATIONS $T_J = 25^\circ\text{C}$, unless otherwise noted								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$		500	-	-	V	
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	Reference to 25°C , $I_D = 1 \text{ mA}$		-	0.63	-	$\text{V}/^\circ\text{C}$	
Gate-source threshold voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$		2.0	-	4.0	V	
Gate-source leakage	I_{GSS}	$V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA	
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 500 \text{ V}$, $V_{GS} = 0 \text{ V}$		-	-	25		
		$V_{DS} = 400 \text{ V}$, $V_{GS} = 0 \text{ V}$, $T_J = 125^\circ\text{C}$		-	-	250	μA	
Drain-source on-state resistance	$R_{DS(\text{on})}$	$V_{GS} = 10 \text{ V}$	$I_D = 12 \text{ A}^b$	-	-	0.27	Λ	
Forward transconductance	g_{fs}	$V_{DS} = 50 \text{ V}$	$I_D = 12 \text{ A}^b$	13	-	-	S	
Dynamic								
Input capacitance	C_{iss}	$V_{GS} = 0 \text{ V}$, $V_{DS} = 25 \text{ V}$, $f = 1.0 \text{ MHz}$, see fig. 5		-	4200	-	pF	
Output capacitance	C_{oss}			-	870	-		
Reverse transfer capacitance	C_{rss}			-	350	-		
Total gate charge	Q_g	$V_{GS} = 10 \text{ V}$	$I_D = 20 \text{ A}$, $V_{DS} = 400 \text{ V}$ see fig. 6 and 13 ^b	-	-	210	nC	
Gate-source charge	Q_{gs}			-	-	29		
Gate-drain charge	Q_{gd}			-	-	110		
Turn-on delay time	$t_{d(on)}$			-	18	-		
Rise time	t_r	$V_{DD} = 250 \text{ V}$, $I_D = 20 \text{ A}$, $R_G = 4.3 \Lambda$, $R_D = 13 \Lambda$, see fig. 10 ^b		-	59	-	ns	
Turn-off delay time	$t_{d(off)}$			-	110	-		
Fall time	t_f			-	58	-		
Internal drain inductance	L_D			-	5.0	-		
Internal source inductance	L_S	Between lead, 6 mm (0.25") from package and center of die contact		-	13	-	nH	
Drain-Source Body Diode Characteristics								
Continuous source-drain diode current	I_S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	20	A	
Pulsed diode forward current ^a	I_{SM}			-	-	80		
Body diode voltage	V_{SD}	$T_J = 25^\circ\text{C}$, $I_S = 20 \text{ A}$, $V_{GS} = 0 \text{ V}^b$		-	-	1.8	V	
Body diode reverse recovery time	t_{rr}	$T_J = 25^\circ\text{C}$, $I_F = 20 \text{ A}$, $dI/dt = 100 \text{ A}/\mu\text{s}^b$		-	570	860	ns	
Body diode reverse recovery charge	Q_{rr}			-	5.7	8.6	μC	
Forward turn-on time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)						

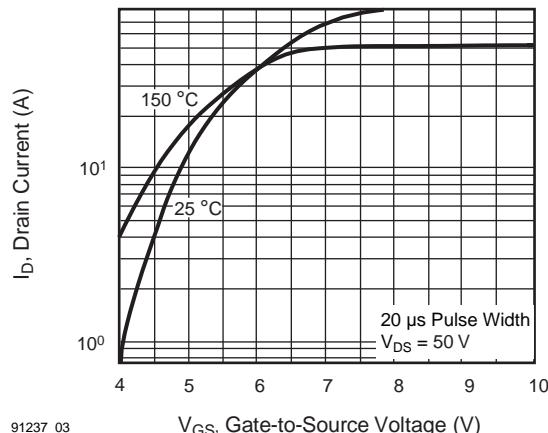
Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
b. Pulse width $\leq 300 \mu\text{s}$; duty cycle $\leq 2\%$

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



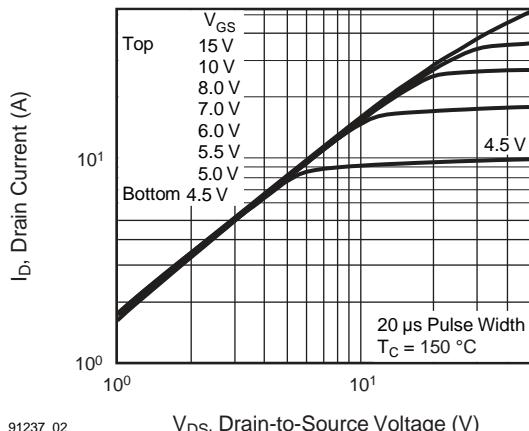
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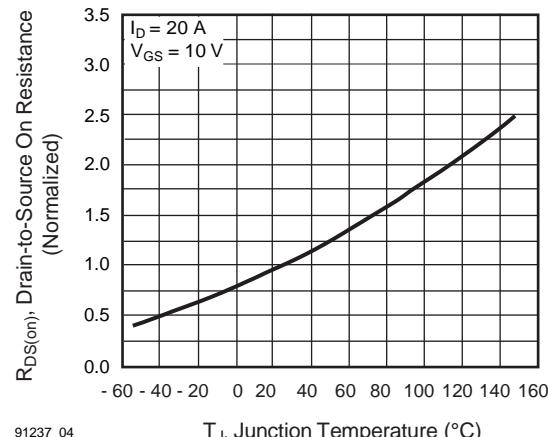
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Fig. 1 - Typical Output Characteristics, $T_c = 25$ °C

Fig. 3 - Typical Transfer Characteristics



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91237_04

Fig. 2 - Typical Output Characteristics, $T_c = 150$ °C

Fig. 4 - Normalized On-Resistance vs. Temperature

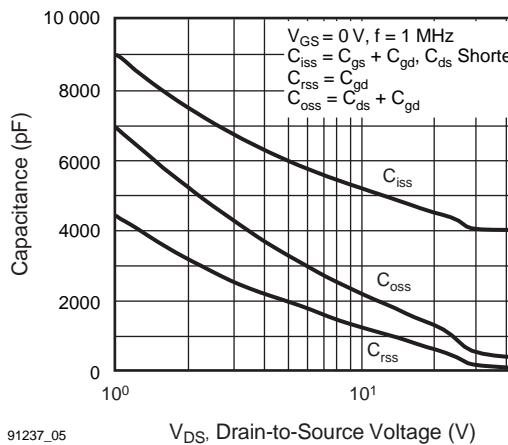


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

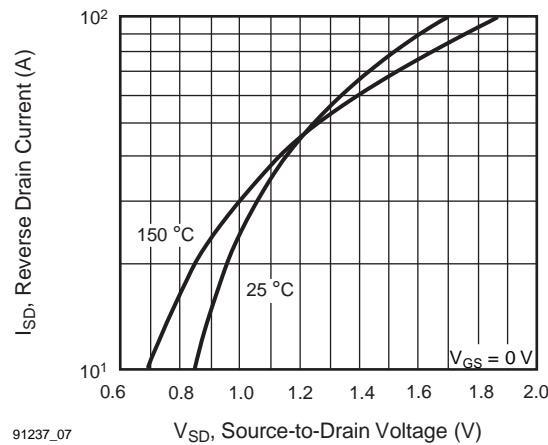


Fig. 7 - Typical Source-Drain Diode Forward Voltage

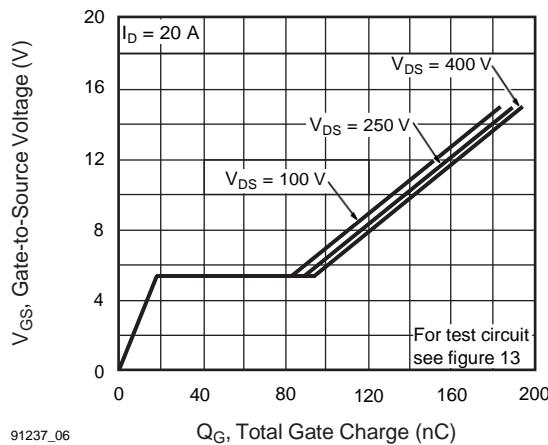


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

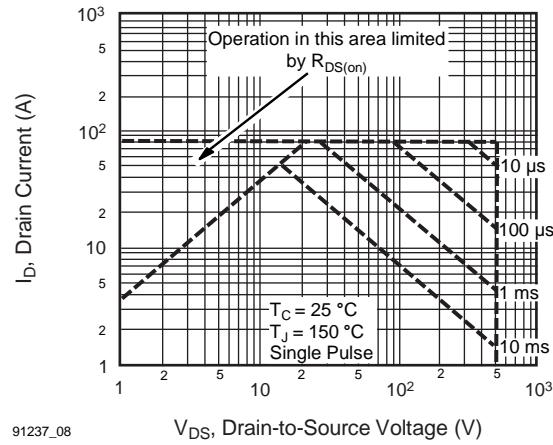
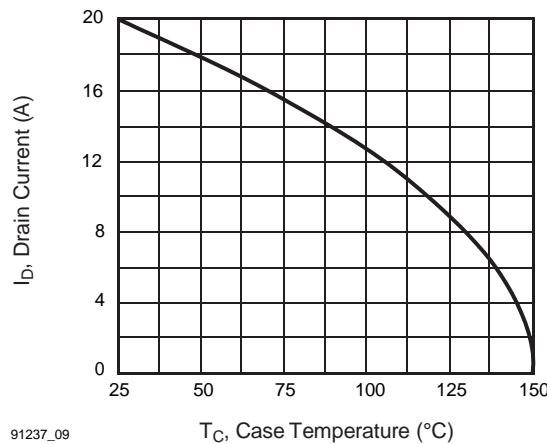
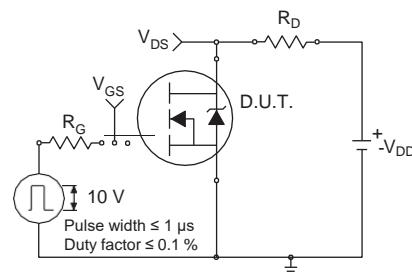
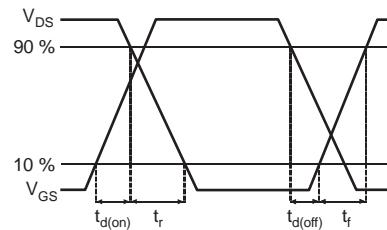
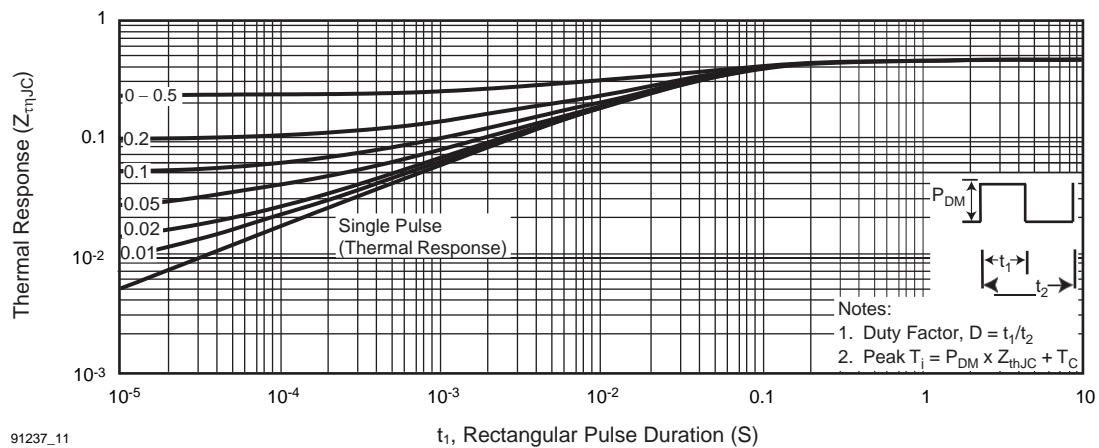
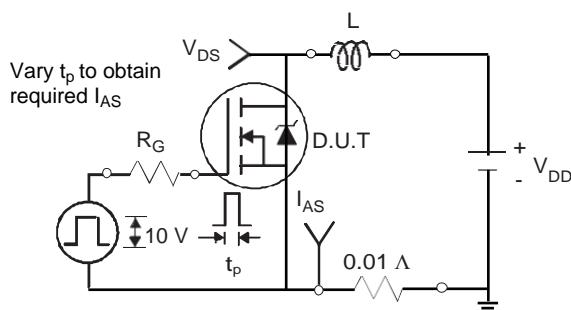
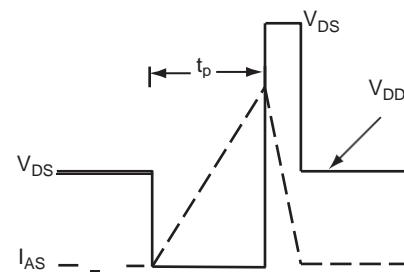
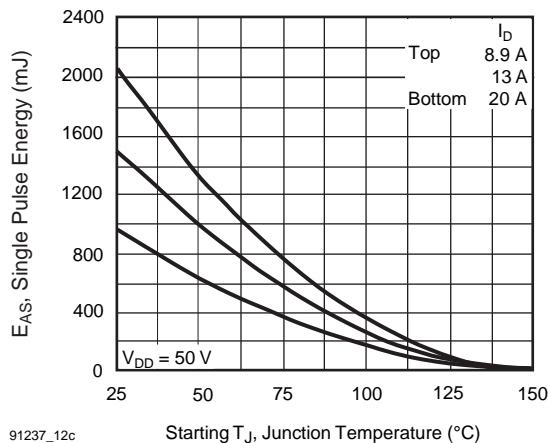
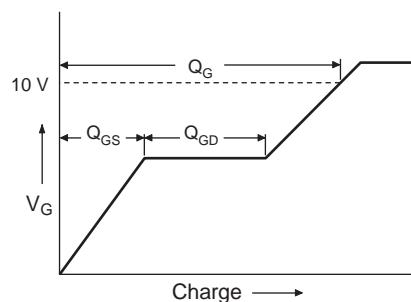
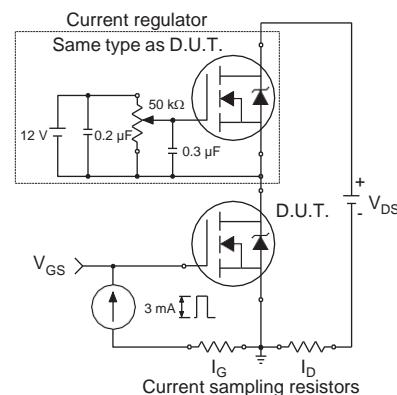


Fig. 8 - Maximum Safe Operating Area


Fig. 9 - Maximum Drain Current vs. Case Temperature

Fig. 10 - Switching Time Test Circuit

Fig. 11 - Switching Time Waveforms

Fig. 12 - Maximum Effective Transient Thermal Impedance, Junction-to-Case


Fig. 13 - Unclamped Inductive Test Circuit

Fig. 14 - Unclamped Inductive Waveforms

Fig. 15 - Maximum Avalanche Energy vs. Drain Current

Fig. 16 - Basic Gate Charge Waveform

Fig. 17 - Gate Charge Test Circuit

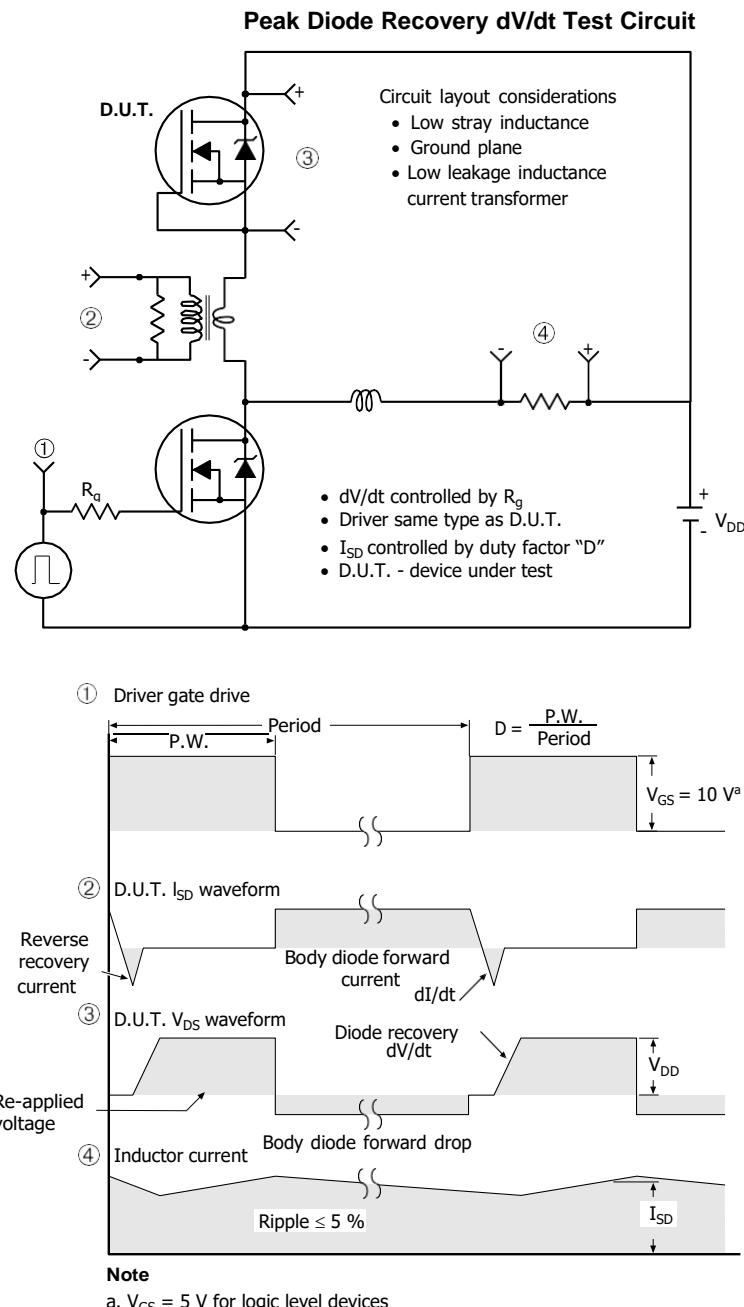
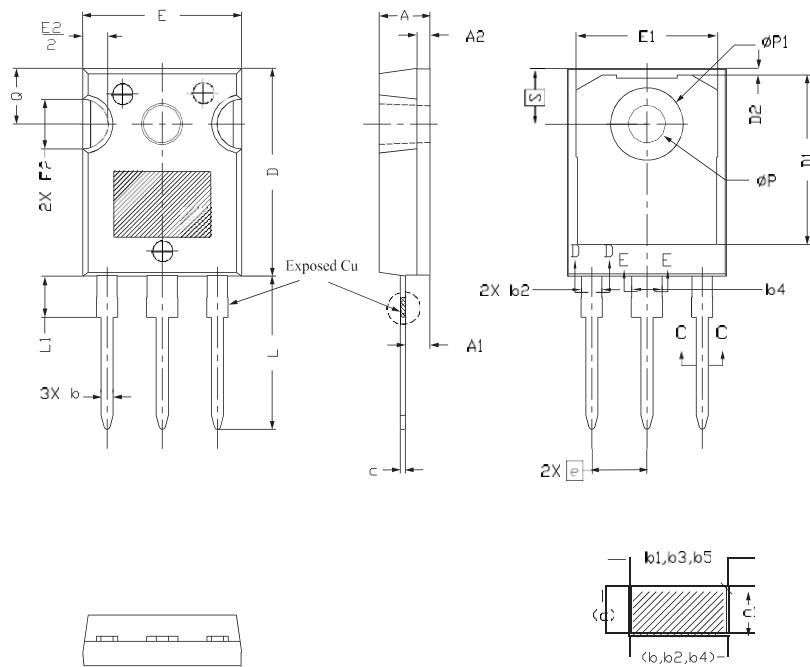


Fig. 18 - For N-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?91237.

TO-247AC (High Voltage)

VERSION 1: FACILITY CODE = 9



Section C-C,D--D,E-E

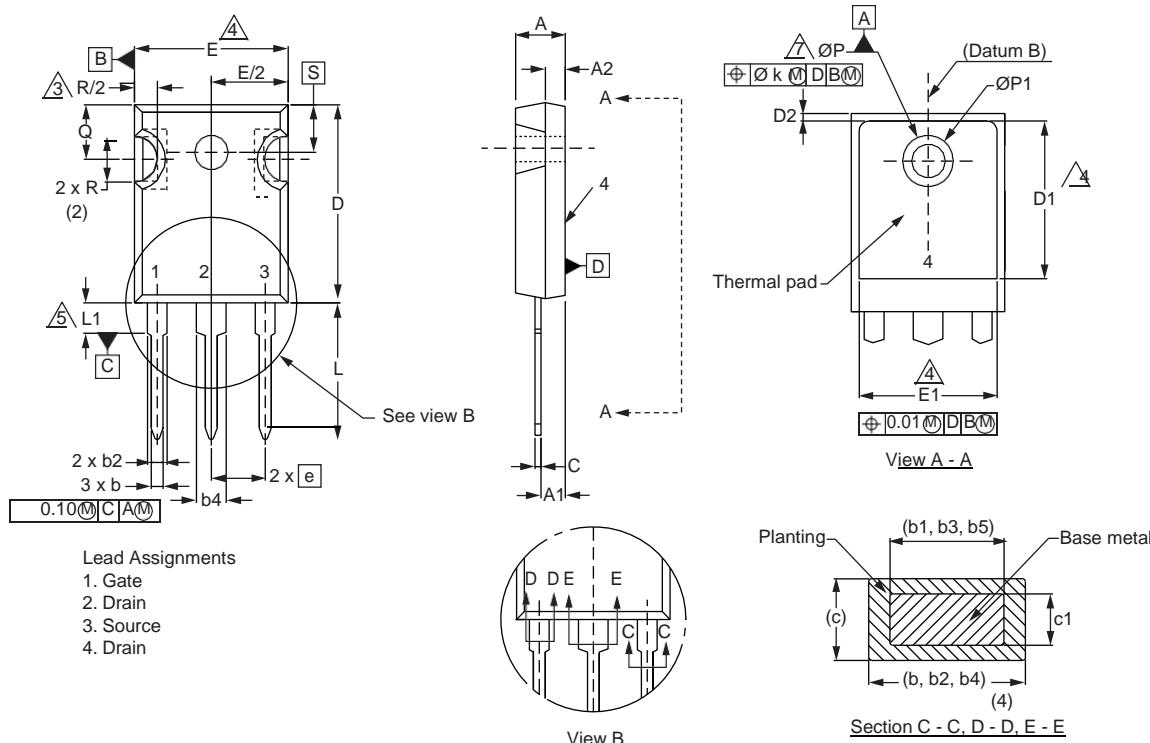
MILLIMETERS				
DIM.	MIN.	NOM.	MAX.	NOTES
A	4.83	5.02	5.21	
A1	2.29	2.41	2.55	
A2	1.17	1.27	1.37	
b	1.12	1.20	1.33	
b1	1.12	1.20	1.28	
b2	1.91	2.00	2.39	6
b3	1.91	2.00	2.34	
b4	2.87	3.00	3.22	6, 8
b5	2.87	3.00	3.18	
c	0.40	0.50	0.60	6
c1	0.40	0.50	0.56	
D	20.40	20.55	20.70	4

Notes

- (1) Package reference: JEDEC® TO247, variation AC
- (2) All dimensions are in mm
- (3) Slot required, notch may be rounded
- (4) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- (5) Thermal pad contour optional with dimensions D1 and E1
- (6) Lead finish uncontrolled in L1
- (7) Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm
- (8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition

MILLIMETERS				
DIM.	MIN.	NOM.	MAX.	NOTES
D1	16.46	16.76	17.06	5
D2	0.56	0.66	0.76	
E	15.50	15.70	15.87	4
E1	13.46	14.02	14.16	5
E2	4.52	4.91	5.49	3
e	5.46 BSC			
L	14.90	15.15	15.40	
L1	3.96	4.06	4.16	6
Ø P	3.56	3.61	3.65	7
Ø P1	7.19 ref.			
Q	5.31	5.50	5.69	
S	5.51 BSC			

VERSION 2: FACILITY CODE = Y

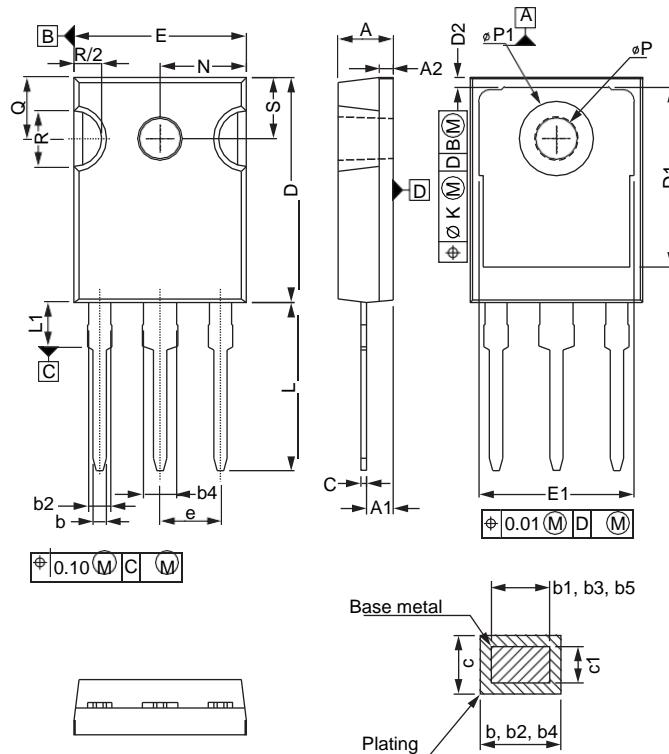


MILLIMETERS			
DIM.	MIN.	MAX.	NOTES
A	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
c	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

MILLIMETERS			
DIM.	MIN.	MAX.	NOTES
D2	0.51	1.30	
E	15.29	15.87	
E1	13.72	-	
e	5.46 BSC		
Ø k	0.254		
L	14.20	16.25	
L1	3.71	4.29	
Ø P	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC outline TO-247 with exception of dimension c

VERSION 3: FACILITY CODE = N


MILLIMETERS		
DIM.	MIN.	MAX.
A	4.65	5.31
A1	2.21	2.59
A2	1.17	1.37
b	0.99	1.40
b1	0.99	1.35
b2	1.65	2.39
b3	1.65	2.34
b4	2.59	3.43
b5	2.59	3.38
c	0.38	0.89
c1	0.38	0.84
D	19.71	20.70
D1	13.08	-

ECN: E22-0452-Rev. G, 31-Oct-2022

DWG: 5971

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

MILLIMETERS		
DIM.	MIN.	MAX.
D2	0.51	1.35
E	15.29	15.87
E1	13.46	-
e	5.46 BSC	
k	0.254	
L	14.20	16.10
L1	3.71	4.29
N	7.62 BSC	
P	3.56	3.66
P1	-	7.39
Q	5.31	5.69
R	4.52	5.49
S	5.51 BSC	

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